



CHENMKO ENTERPRISE CO.,LTD

CHT1544RNPT

**SURFACE MOUNT
Dual Silicon Transistor**

VOLTAGE 20 Volts CURRENT 300 mAmpere

Lead free devices

APPLICATION

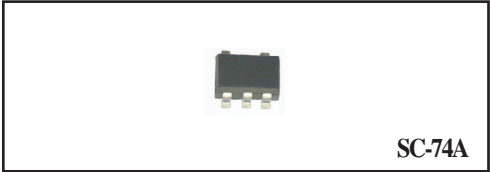
* Switching circuit, Inverter, Interface circuit, Driver circuit.

FEATURE

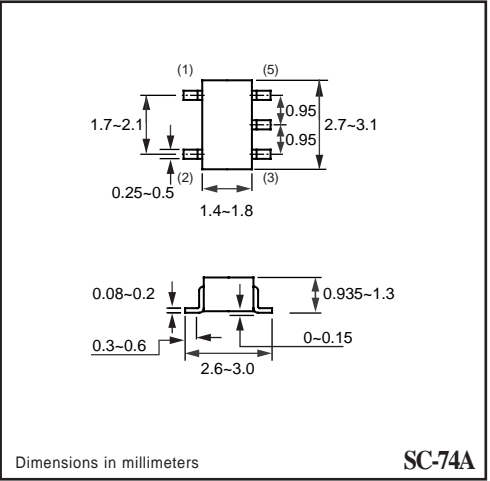
- * Small surface mounting type. (SC-74A)
- * High current gain.
- * Suitable for high packing density.
- * Low collector-emitter saturation.
- * High saturation current capability.
- * Both the NPN digital silicon transistor in one package.
- * Built in bias resistor(R1=2.2kΩ, Typ.)

MARKING

- *HFE(A) : 44A
- *HFE(B) : 44B

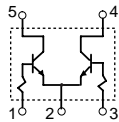


SC-74A



SC-74A

CIRCUIT



LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-Base voltage		50	V
V _{CEO}	Collector-Emitter voltage		20	V
V _{EBO}	Emitter-Base voltage		25	V
I _c	Collector current		300	mA
P _D	Collector Power dissipation	T _{amb} ≤ 25 °C, Note 1	300	mW
T _{STG}	Storage temperature		-55 +150	°C
T _J	Junction temperature		+150	°C
Rθ _{J-S}	Thermal resistance , Note 1	junction - soldering point	350	°C/W

Note

1. Total rating

RATING CHARACTERISTIC (CHT1544RNPT)

CHARACTERISTICS

$T_{amb} = 25\text{ }^{\circ}\text{C}$ unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I_{CBO}	Collector cutoff current	$V_{CB}=50V$	–	–	0.1	μA
I_{EBO}	Emitter cutoff current	$V_{EB}=25V$	–	–	0.1	μA
$V_{CE(sat)}$	Collector-emitter saturation voltage	$I_C/I_B=10\text{mA}/1\text{mA}$	–	–	0.1	V
h_{FE}	DC current gain	$I_C=4\text{mA}; V_{CE}=2.0V$	200	–	1200	
R_1	Input resistor		1.54	2.2	2.86	$\text{K}\Omega$
f_T	Transition frequency	$I_C=4\text{mA}, V_{CE}=6.0V$	–	30	–	MHz

Note

1. h_{FE} Classification A: 200 to 700, B: 350 to 1200

RATING CHARACTERISTIC CURVES (CHT1544RNPT)

Typical Electrical Characteristics

Fig.1 DC current gain vs. collector current

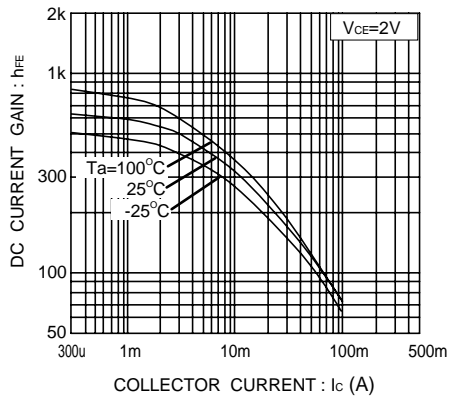


Fig.2 Collector-emitter saturation voltage vs. collector current

